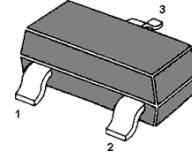


## MMBTSC2785 NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups O, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1.Base 2.Emitter 3.Collector  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	60	V
Collector Emitter Voltage	$V_{CEO}$	50	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	150	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +150	$^\circ\text{C}$

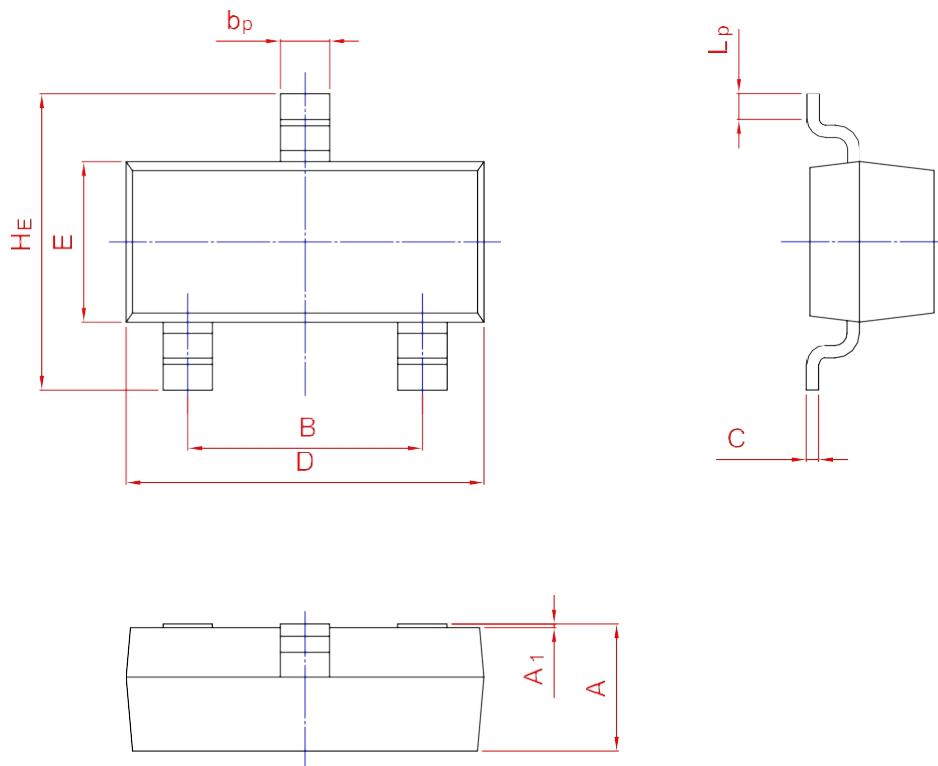
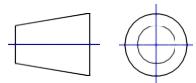
**Characteristics at  $T_{amb}=25^{\circ}C$** 

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=6V$ , $I_C=1mA$	$h_{FE}$	70	-	140	-
	$h_{FE}$	120	-	240	-
	$h_{FE}$	200	-	400	-
	$h_{FE}$	350	-	700	-
Collector Base Breakdown Voltage at $I_C=100\mu A$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C=10mA$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu A$	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $V_{CB}=40V$	$I_{CBO}$	-	-	0.1	$\mu A$
Emitter Cutoff Current at $V_{EB}=3V$	$I_{EBO}$	-	-	0.1	$\mu A$
Collector Saturation Voltage at $I_C=100mA$ , $I_B=10mA$	$V_{CE(sat)}$	-	-	0.3	V
Gain Bandwidth Product at $V_{CE}=6V$ , $I_C=10mA$	$f_T$	-	300	-	MHz
Output Capacitance at $V_{CB}=6V$ , $f=1MHz$	$C_{OB}$	-	2.5	-	pF
Noise Figure at $V_{CE}=6V$ , $I_E=0.5mA$ , $f=1KHz$ , $R_S=500\Omega$	NF	-	4	-	dB

## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	2.70 1.20	3.10 1.65	3.00 2.20	0.100 0.013	0.50 0.20